

## REMARKS

Supplementing the amendment filed May 18, 2001, claim 98 is amended to consistently refer to a "first dopant type."

Claims 43-107 are pending.

In the Amendment filed May 18, 2001, at Remarks, page 13, line 19, "polysilicon, et al." should read --polysilicon or metal-- and subsection "35 USC § Rejections," at page 16, after line 18, insert "in view of Davis, Blanchard and Wickstrom."

For the Examiner's convenience, enclosed are copies of applicant's prior patents 4,895,810; 5,045,903 and 5,262,336 from which priority is claimed in the present application.

Attached is a Version With Markings to Show Changes Made To Claims by the current amendment.

The application should now be in condition for allowance. If any questions remain, the Examiner is requested to call the undersigned.



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PATENT TRADEMARK OFFICE

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE TO CLAIMS

98. (Amended) A power MOSFET comprising:

a semiconductor substrate, the substrate comprising drain semiconductor material of a first [type] dopant type;

source semiconductor material of a dopant type the same as said first dopant type;

channel semiconductor material of a second dopant type disposed between the source semiconductor material and the drain semiconductor material, the channel semiconductor material operative under field effect to conduct current between the source semiconductor material and the drain semiconductor material;

a conductive gate structure configured to enable provision of a field to the channel semiconductor material;

a gate oxide layer disposed between the conductive gate structure and the channel semiconductor material;

said conductive gate structure comprising doped polysilicon contacting the oxide layer and metal disposed coextensively over the doped polysilicon;

an insulating layer disposed over said gate structure; and

metallization over said insulating layer, the metallization contacting the gate structure through said insulating layer.